

# Gunter Semiconductor GmbH

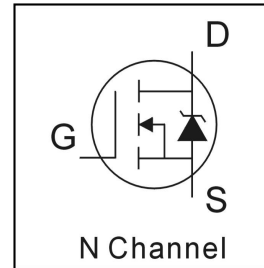
# GFC130

## N Channel Power MOSFET

## Chip Specification

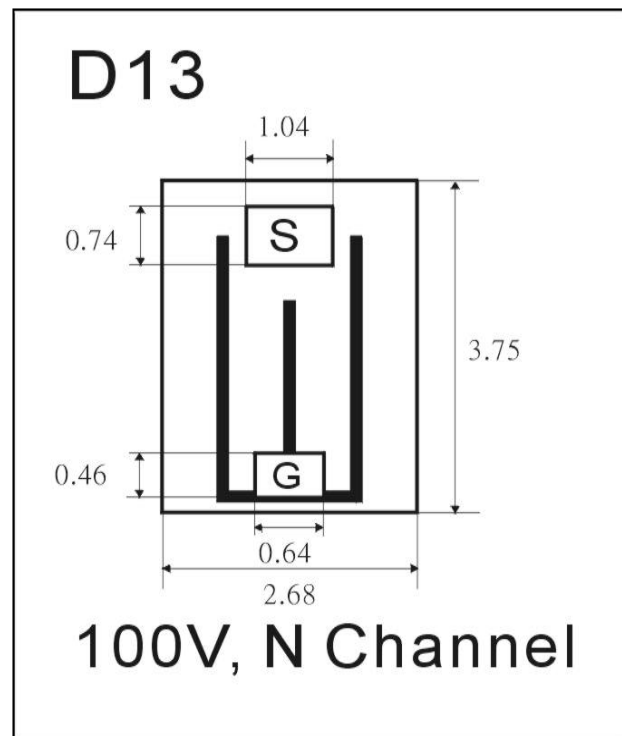
### General Description:

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **175°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**



### Mechanical Data:

<b>D13</b>
Dimension <b>2.68mm x 3.75mm</b>
Thickness: <b>400 μm</b>
Metallization:
Top : : <b>Al</b>
Backside : <b>CrNiAg / Au</b>
Suggested Bonding Conditions:
Die Mounting: <b>Solder Perform</b>
<b>95/5 PbSn or 92.5/2.5/5 PbAgIn</b>
Source Bonding Wire: <b>10 mil Al</b>



### Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	100	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.16	Ω	VGS=10V, ID=9A
Continuous Drain current ( in target package)	ID@25°C	15	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	11	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

### Target Device: IRF530

TO-220AB

PD

63

W

@Tc=25°C

